

Chang Seok Kang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11484111/publications.pdf>

Version: 2024-02-01

30
papers

1,271
citations

471509

17
h-index

580821

25
g-index

30
all docs

30
docs citations

30
times ranked

820
citing authors

#	ARTICLE	IF	CITATIONS
1	A comparative study on the electrical conduction mechanisms of (Ba _{0.5} Sr _{0.5})TiO ₃ thin films on Pt and IrO ₂ electrodes. Journal of Applied Physics, 1998, 83, 3703-3713.	2.5	168
2	Bonding states and electrical properties of ultrathin HfO _x N _y gate dielectrics. Applied Physics Letters, 2002, 81, 2593-2595.	3.3	154
3	Depletion layer thickness and Schottky type carrier injection at the interface between Pt electrodes and (Ba, $\hat{\epsilon}$ %Sr)TiO ₃ thin films. Journal of Applied Physics, 1999, 85, 287-295.	2.5	134
4	Bias-temperature instabilities of polysilicon gate HfO ₂ /MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 1517-1524.	3.0	110
5	The Electrical and Material Characterization of Hafnium Oxynitride Gate Dielectrics With TaN-Gate Electrode. IEEE Transactions on Electron Devices, 2004, 51, 220-227.	3.0	92
6	Deposition and Electrical Characterization of Very Thin SrTiO ₃ Films for Ultra Large Scale Integrated Dynamic Random Access Memory Application. Japanese Journal of Applied Physics, 1995, 34, 5178-5183.	1.5	80
7	Improvement of surface carrier mobility of HfO ₂ /MOSFETs by high-temperature forming gas annealing. IEEE Transactions on Electron Devices, 2003, 50, 384-390.	3.0	80
8	Electrical characterization and material evaluation of zirconium oxynitride gate dielectric in TaN-gated NMOSFETs with high-temperature forming gas annealing. IEEE Transactions on Electron Devices, 2003, 50, 333-340.	3.0	52
9	Preparation and Electrical Properties of SrTiO ₃ Thin Films Deposited by Liquid Source Metal-Organic Chemical Vapor Deposition (MOCVD). Japanese Journal of Applied Physics, 1996, 35, 4890-4895.	1.5	51
10	Structural and electrical properties of HfO ₂ with top nitrogen incorporated layer. IEEE Electron Device Letters, 2002, 23, 249-251.	3.9	45
11	Evaluation of silicon surface nitridation effects on ultra-thin ZrO ₂ gate dielectrics. Applied Physics Letters, 2002, 81, 1663-1665.	3.3	40
12	Area dependence of TDDDB characteristics for HfO ₂ gate dielectrics. IEEE Electron Device Letters, 2002, 23, 594-596.	3.9	34
13	A positive temperature coefficient of resistivity effect from a paraelectric Pt/(Ba _{0.5} ,Sr _{0.5})TiO ₃ /IrO ₂ thin-film capacitor. Applied Physics Letters, 1997, 71, 371-373.	3.3	32
14	Deposition Characteristics of (Ba,Sr)TiO ₃ Thin Films by Liquid Source Metal-Organic Chemical Vapor Deposition at Low Substrate Temperatures. Japanese Journal of Applied Physics, 1997, 36, 6946-6952.	1.5	31
15	Interface potential barrier height and leakage current behavior of Pt/(Ba, Sr)TiO ₃ /Pt capacitors fabricated by sputtering process. Integrated Ferroelectrics, 1996, 13, 157-177.	0.7	26
16	Effects of varying interfacial oxide and high-k layer thicknesses for HfO ₂ metal-oxide-semiconductor field effect transistor. Applied Physics Letters, 2004, 85, 1286-1288.	3.3	24
17	Effects of high temperature forming gas anneal on the characteristics of metal-oxide-semiconductor field-effect transistor with HfO ₂ gate stack. Applied Physics Letters, 2004, 84, 4839-4841.	3.3	19
18	Effects of deuterium anneal on MOSFETs with HfO ₂ gate dielectrics. IEEE Electron Device Letters, 2003, 24, 144-146.	3.9	18

#	ARTICLE	IF	CITATIONS
19	High-quality ultra-thin HfO ₂ /gate dielectric MOSFETs with TaN electrode and nitridation surface preparation. , 0, , .		16
20	Effects of oxidants on the deposition and dielectric properties of the SrTiO ₃ thin films prepared by liquid source metal-organic chemical vapor deposition (MOCVD). Integrated Ferroelectrics, 1996, 12, 199-213.	0.7	12
21	Effects of dielectric structure of HfO ₂ on carrier generation rate in Si substrate and channel mobility. Applied Physics Letters, 2004, 84, 2148-2150.	3.3	12
22	Performance of polysilicon gate HfO ₂ MOSFETs on [100] and [111] silicon substrates. IEEE Electron Device Letters, 2003, 24, 254-256.	3.9	10
23	Scaling down of ultrathin HfO ₂ gate dielectrics by using a nitrided Si surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 916.	1.6	8
24	Dopant penetration effects on polysilicon gate HfO ₂ /MOSFET's. , 0, , .		7
25	Threshold voltage instability characteristics under positive dynamic stress in ultrathin HfO ₂ metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2004, 85, 3184-3186.	3.3	7
26	Effects of Hf contamination on the properties of silicon oxide metal-oxide-semiconductor devices. Applied Physics Letters, 2002, 81, 5018-5020.	3.3	4
27	Dynamic positive bias temperature instability characteristics of ultra-thin HfO ₂ /NMOSFET. , 0, , .		3
28	Effects of nitrogen-incorporated interface layer on the transient characteristics of hafnium oxide n-metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2005, 86, 123506.	3.3	2
29	Variations of interface potential barrier height and leakage current of (Ba, Sr)TiO ₃ thin films deposited by sputtering process. Integrated Ferroelectrics, 1998, 20, 255-255.	0.7	0
30	Performance effects of two nitrogen incorporation techniques on TaN/HfO ₂ and poly/HfO ₂ /MOSCAP and MOSFET devices. , 0, , .		0